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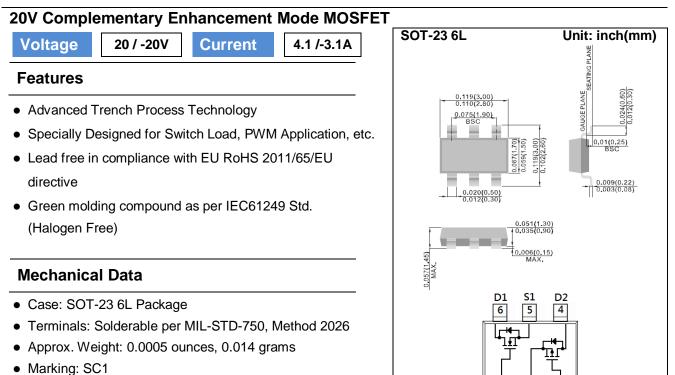
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#### PJS6601



#### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	20	-20	V
Gate-Source Voltage	$V_{GS}$	<u>+</u> 12	<u>+</u> 12	V	
Continuous Drain Current	I <sub>D</sub>	4.1	-3.1	А	
Pulsed Drain Current (Note 4)	I <sub>DM</sub>	16.4	-12.4	А	
	T <sub>a</sub> =25°C	5	1.25		W
Power Dissipation	Derate above 25°C	P <sub>D</sub>	1	mW/°C	
Operating Junction and Storage Tem	$T_{J},T_{STG}$	-55~150		°C	
Typical Thermal Resistance - Junction to Ambient <sup>(Note 3)</sup>		R <sub>θJA</sub>	100		°C/W



#### N-Channel Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.4	0.66	1.2	V
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.1A	-	41	56	mΩ
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.8A	-	50	68	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =1.5A	-	66	95	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =20V, $V_{GS}$ =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 5)						
Total Gate Charge	Qg		-	4.6	-	
Gate-Source Charge	$Q_gs$	$V_{DS}$ =10V, I <sub>D</sub> =4.1A, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	0.8	-	nC
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =4.5V	-	1	-	
Input Capacitance	Ciss	$V_{DS}$ =10V, $V_{GS}$ =0V,	-	350	-	
Output Capacitance	Coss		-	40	-	pF
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	29	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	4	-	
Turn-On Rise Time	tr	$V_{DD}=10V, I_{D}=4.1A,$	-	47	-	
Turn-Off Delay Time	td <sub>(off)</sub>	$V_{GS}$ =4.5V, R <sub>G</sub> =6 $\Omega$ <sup>(Note 1,2)</sup>	-	18	-	ns
Turn-Off Fall Time	tf	K <sub>G</sub> =012	-	10	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>		-	-	1.5	А
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	0.75	1.2	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ReJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing



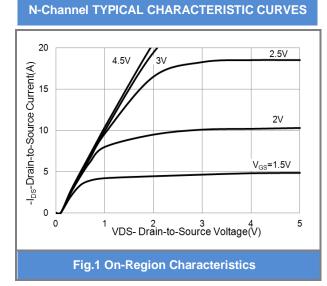
#### **P-Channel Electrical Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static	STMBOL	TEST CONDITION	IVIIIN.	116.		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250$ uA	-0.4	-0.71	-1.2	V
Drain-Source On-State Resistance	00()	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.1A	-	84	100	mΩ
	R <sub>DS(on)</sub>	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2.0A	-	104	135	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-1.1A	-	134	190	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =-20V, $V_{GS}$ =0V	-	-	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 5)						
Total Gate Charge	Qg	$V_{DS}$ =-10V, $I_{D}$ =-3.1A,	-	5.4	-	
Gate-Source Charge	$Q_gs$		-	0.7	-	nC
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	1.3	-	
Input Capacitance	Ciss	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1.0MHZ	-	416	-	
Output Capacitance	Coss		-	43	-	pF
Reverse Transfer Capacitance	Crss		-	32	-	
Turn-On Delay Time	td <sub>(on)</sub>	V 40V L 24A	-	4	-	
Turn-On Rise Time	tr	$V_{DD}$ =-10V, I <sub>D</sub> =-3.1A, $V_{GS}$ =-4.5V, $R_{G}$ =6 $\Omega$ <sup>(Note 1,2)</sup>	-	27	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	78	-	ns
Turn-Off Fall Time	tf		-	45	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					1 5	
Diode Forward Current	I <sub>S</sub>		-	-	-1.5	A
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V	-	-0.8	-1.2	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. R<sub>OJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





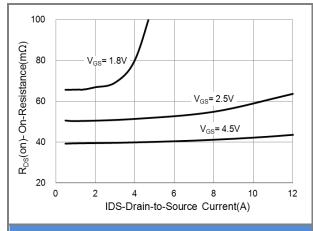
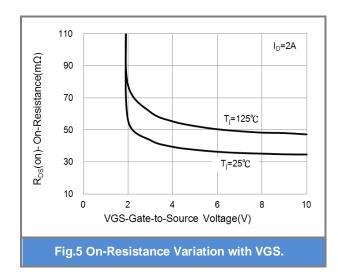
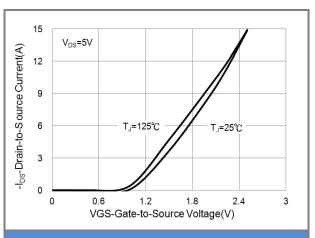


Fig.3 On-Resistance vs. Drain Current







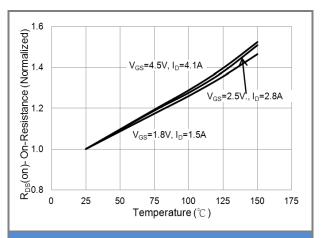
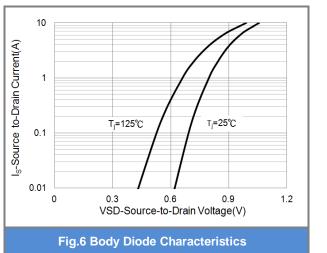


Fig.4 On-Resistance vs. Junction temperature





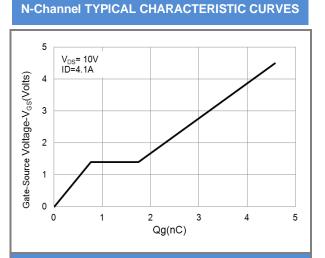


Fig.7 Gate-Charge Characteristics

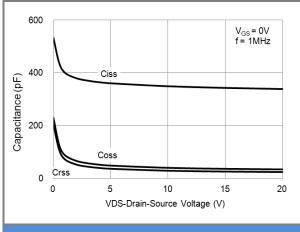
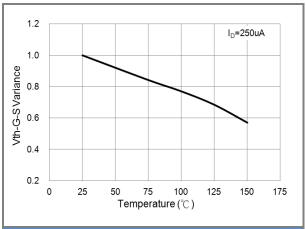


Fig.9 Capacitance vs. Drain-Source Voltage.

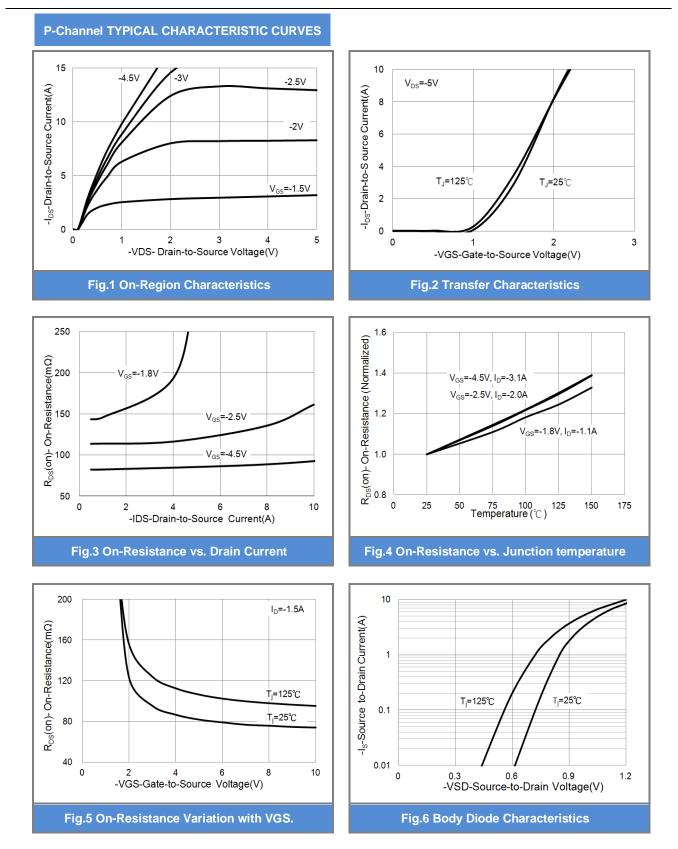






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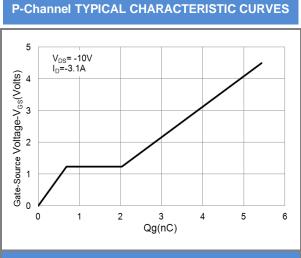


Fig.7 Gate-Charge Characteristics

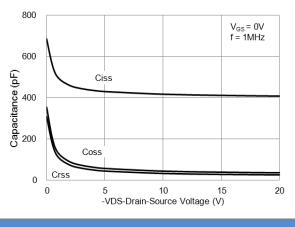
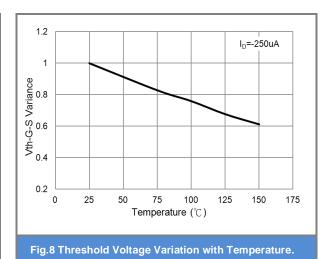


Fig.9 Threshold Voltage Variation with Temperature.



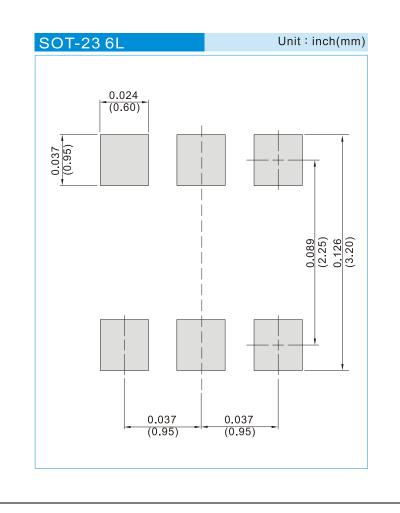




#### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJS6601_S1_00001	SOT-23 6L	3K pcs / 7" reel	SC1	Halogen free
PJS6601_S2_00001	SOT-23 6L	10K pcs / 13" reel	SC1	Halogen free

#### MOUNTING PAD LAYOUT





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